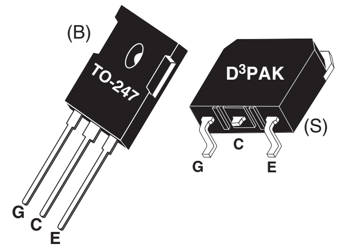
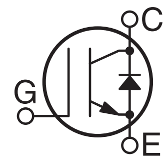
POWER PRODUCTS GROUP

*G Denotes RoHS Compliant, Pb Free Terminal Finish.

Utilizing the latest Field Stop and Trench Gate technologies, these IGBT's have ultra low $V_{CE(ON)}$ and are ideal for low frequency applications that require absolute minimum conduction loss. Easy paralleling is a result of very tight parameter distribution and a slightly positive $V_{CE(ON)}$ temperature coefficient. Low gate charge simplifies gate drive design and minimizes losses.



- **600V Field Stop**
- **Trench Gate: Low $V_{CE(on)}$**
- **Easy Paralleling**
- **6µs Short Circuit Capability**
- **175°C Rated**



Applications: Welding, Inductive Heating, Solar Inverters, SMPS, Motor drives, UPS

MAXIMUM RATINGS

All Ratings: T_C = 25°C unless otherwise specified.

Symbol	Parameter	APT20GN60BD_SDQ1(G)	UNIT
V_{CES}	Collector-Emitter Voltage	600	Volts
V_{GE}	Gate-Emitter Voltage	±30	
I_{C1}	Continuous Collector Current @ T_C = 25°C	40	Amps
I_{C2}	Continuous Collector Current @ T_C = 110°C	24	
I_{CM}	Pulsed Collector Current ① @ T_C = 175°C	60	
SSOA	Switching Safe Operating Area @ T_J = 175°C	60A @ 600V	
P_D	Total Power Dissipation	136	Watts
T_J,T_{STG}	Operating and Storage Junction Temperature Range	-55 to 175	°C
T_L	Max. Lead Temp. for Soldering: 0.063" from Case for 10 Sec.	300	

STATIC ELECTRICAL CHARACTERISTICS

Symbol	Characteristic / Test Conditions	MIN	TYP	MAX	Units
$V_{(BR)CES}$	Collector-Emitter Breakdown Voltage (V_{GE} = 0V, I_C = 2mA)	600			Volts
$V_{GE(TH)}$	Gate Threshold Voltage (V_{CE} = V_{GE}, I_C = 290µA, T_j = 25°C)	5.0	5.8	6.5	
$V_{CE(ON)}$	Collector-Emitter On Voltage (V_{GE} = 15V, I_C = 20A, T_j = 25°C)	1.1	1.5	1.9	
	Collector-Emitter On Voltage (V_{GE} = 15V, I_C = 20A, T_j = 125°C)		1.7		
I_{CES}	Collector Cut-off Current (V_{CE} = 600V, V_{GE} = 0V, T_j = 25°C) ②			50	µA
	Collector Cut-off Current (V_{CE} = 600V, V_{GE} = 0V, T_j = 125°C) ②			TBD	
I_{GES}	Gate-Emitter Leakage Current (V_{GE} = ±20V)			300	nA
$R_{G(int)}$	Intergrated Gate Resistor		N/A		Ω

CAUTION: These Devices are Sensitive to Electrostatic Discharge. Proper Handling Procedures Should Be Followed.

050-7615 Rev B 7-2009

DYNAMIC CHARACTERISTICS

Symbol	Characteristic	Test Conditions	MIN	TYP	MAX	UNIT
C_{ies}	Input Capacitance	**Capacitance** V_{GE} = 0V, V_{CE} = 25V f = 1 MHz		1110		pF
C_{oes}	Output Capacitance			50		
C_{res}	Reverse Transfer Capacitance			35		
V_{GEP}	Gate-to-Emitter Plateau Voltage	Gate Charge V_{GE} = 15V V_{CE} = 300V I_C = 20A		9.5		V
Q_g	Total Gate Charge ③			120		nC
Q_{ge}	Gate-Emitter Charge			10		
Q_{gc}	Gate-Collector ("Miller") Charge			70		
SSOA	Switching Safe Operating Area	T_J = 175°C, R_G = 4.3Ω⑦, V_{GE} = 15V, L = 100µH, V_{CE} = 600V	60			A
SCSOA	Short Circuit Safe Operating Area	V_{CC} = 360V, V_{GE} = 15V, T_J = 150°C, R_G = 4.3Ω⑦	6			µs
$t_{d(on)}$	Turn-on Delay Time	**Inductive Switching (25°C)** V_{CC} = 400V V_{GE} = 15V I_C = 20A R_G = 4.3Ω⑦ T_J = +25°C		9		ns
t_r	Current Rise Time			10		
$t_{d(off)}$	Turn-off Delay Time			140		
t_f	Current Fall Time			95		
E_{on1}	Turn-on Switching Energy ④			230		µJ
E_{on2}	Turn-on Switching Energy (Diode) ⑤			260		
E_{off}	Turn-off Switching Energy ⑥			580		
$t_{d(on)}$	Turn-on Delay Time	**Inductive Switching (125°C)** V_{CC} = 400V V_{GE} = 15V I_C = 20A R_G = 4.3Ω⑦ T_J = +125°C		9		ns
t_r	Current Rise Time			10		
$t_{d(off)}$	Turn-off Delay Time			160		
t_f	Current Fall Time			130		
E_{on1}	Turn-on Switching Energy ④			250		µJ
E_{on2}	Turn-on Switching Energy (Diode) ⑤			450		
E_{off}	Turn-off Switching Energy ⑥			750		

THERMAL AND MECHANICAL CHARACTERISTICS

Symbol	Characteristic	MIN	TYP	MAX	UNIT
$R_{\theta JC}$	Junction to Case **(IGBT)**			1.1	°C/W
$R_{\theta JC}$	Junction to Case **(DIODE)**			1.35	
W_T	Package Weight		5.9		gm

① Repetitive Rating: Pulse width limited by maximum junction temperature.

② For Combi devices, I_{ces} includes both IGBT and FRED leakages

③ See MIL-STD-750 Method 3471.

④ E_{on1} is the clamped inductive turn-on energy of the IGBT only, without the effect of a commutating diode reverse recovery current adding to the IGBT turn-on loss. Tested in inductive switching test circuit shown in figure 21, but with a Silicon Carbide diode.

⑤ E_{on2} is the clamped inductive turn-on energy that includes a commutating diode reverse recovery current in the IGBT turn-on switching loss. (See Figures 21, 22.)

⑥ E_{off} is the clamped inductive turn-off energy measured in accordance with JEDEC standard JESD24-1. (See Figures 21, 23.)

⑦ R_G is external gate resistance, not including $R_{G(int)}$ nor gate driver impedance. (MIC4452)

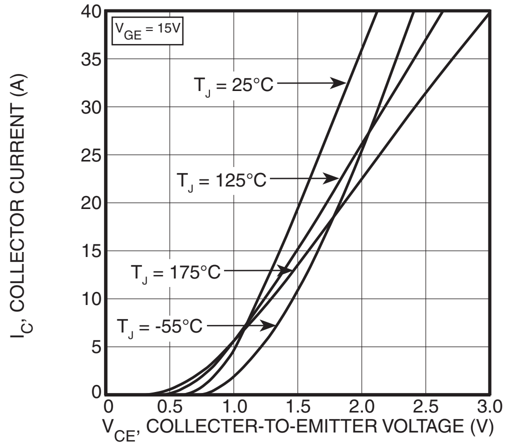


FIGURE 1, Output Characteristics(T_J = 25°C)

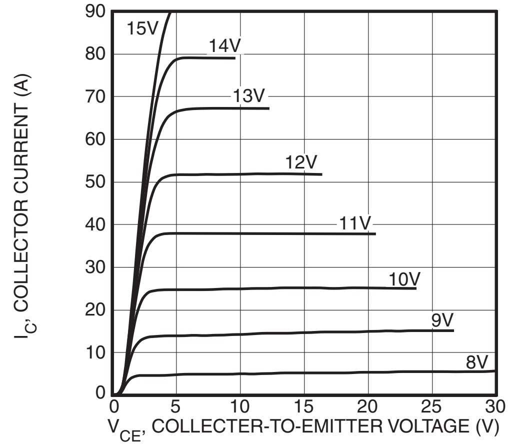


FIGURE 2, Output Characteristics (T_J = 125°C)

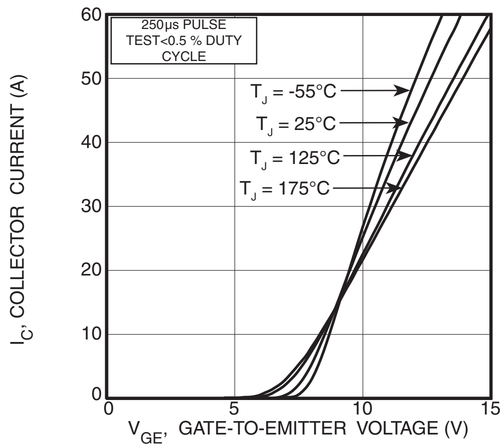


FIGURE 3, Transfer Characteristics

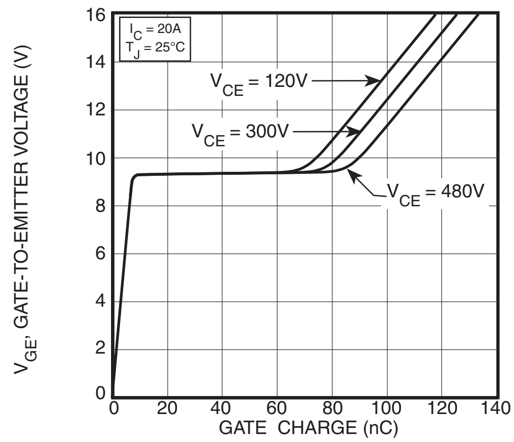


FIGURE 4, Gate Charge

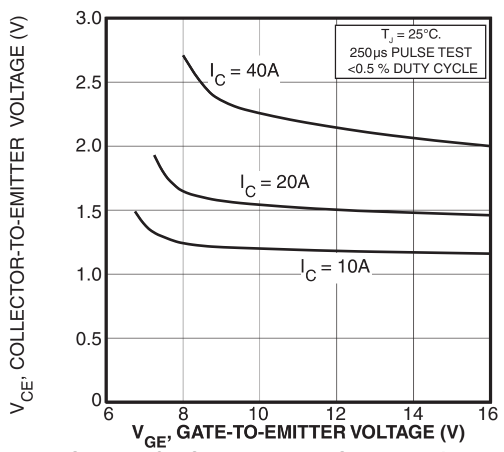


FIGURE 5, On State Voltage vs Gate-to- Emitter Voltage

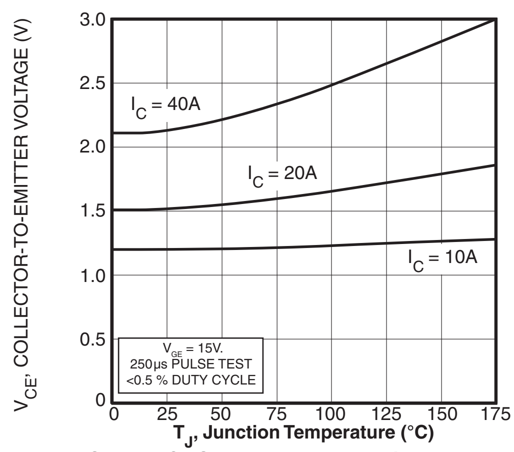


FIGURE 6, On State Voltage vs Junction Temperature

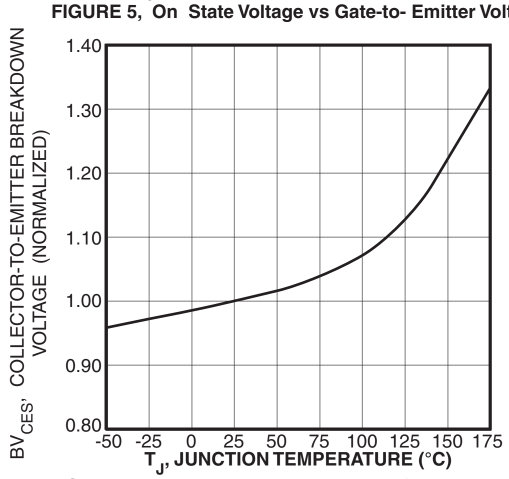


FIGURE 7, Breakdown Voltage vs. Junction Temperature

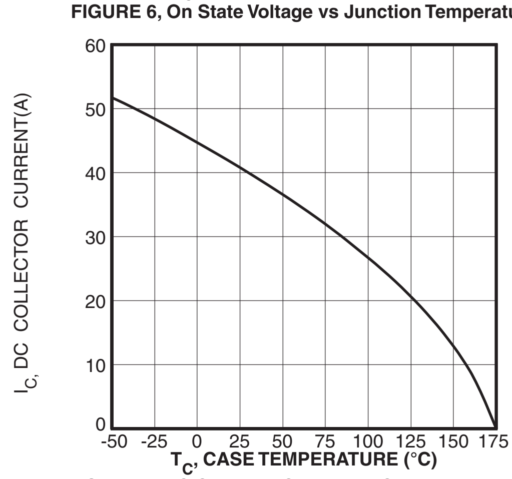


FIGURE 8, DC Collector Current vs Case Temperature

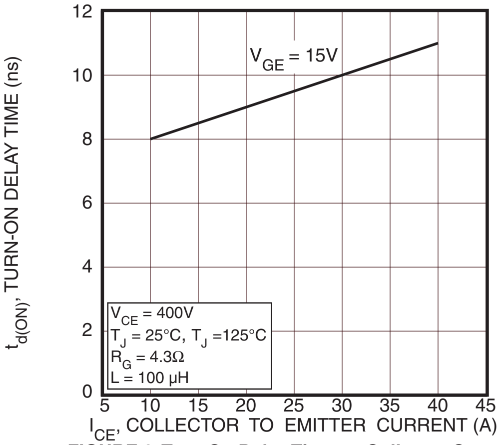


FIGURE 9, Turn-On Delay Time vs Collector Current

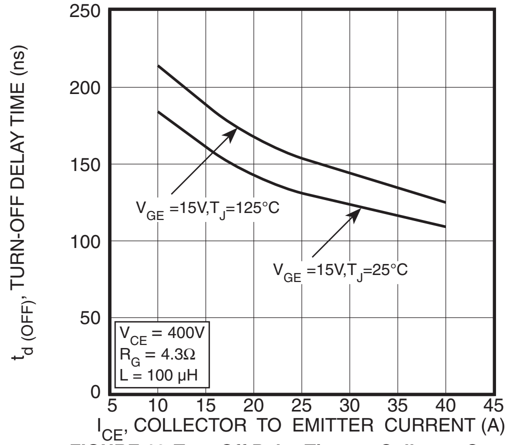


FIGURE 10, Turn-Off Delay Time vs Collector Current

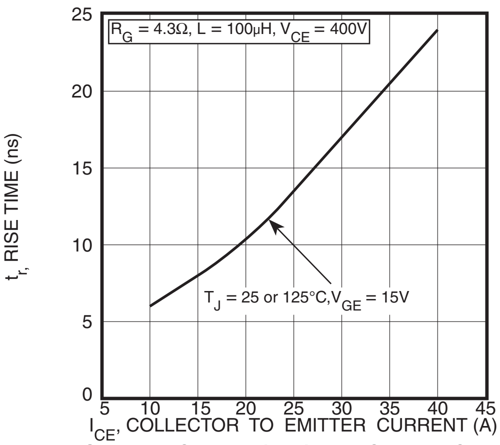


FIGURE 11, Current Rise Time vs Collector Current

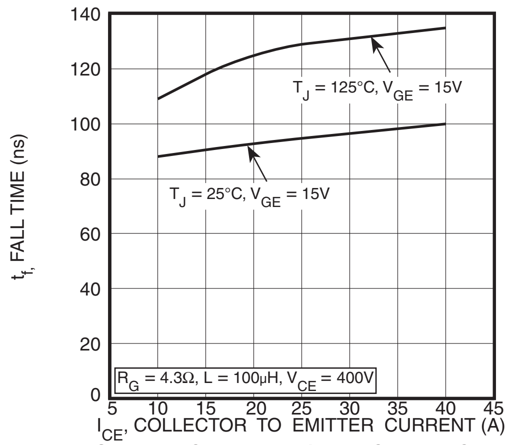


FIGURE 12, Current Fall Time vs Collector Current

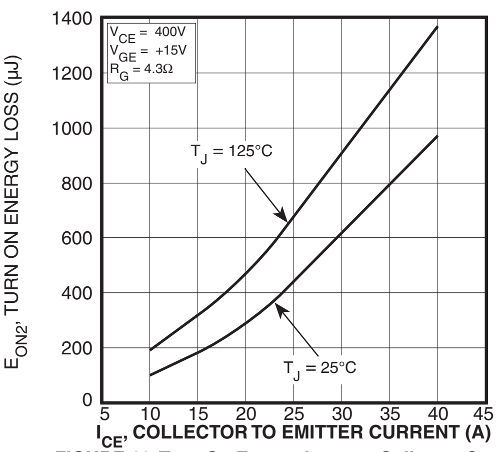


FIGURE 13, Turn-On Energy Loss vs Collector Current

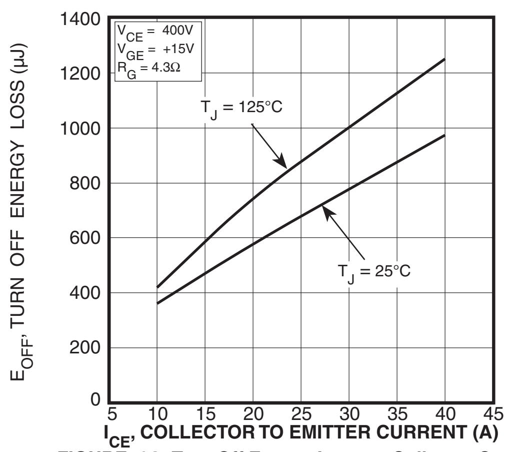


FIGURE 14, Turn Off Energy Loss vs Collector Current

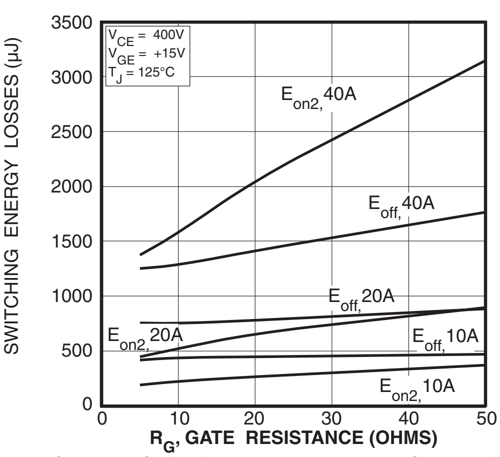


FIGURE 15, Switching Energy Losses vs. Gate Resistance

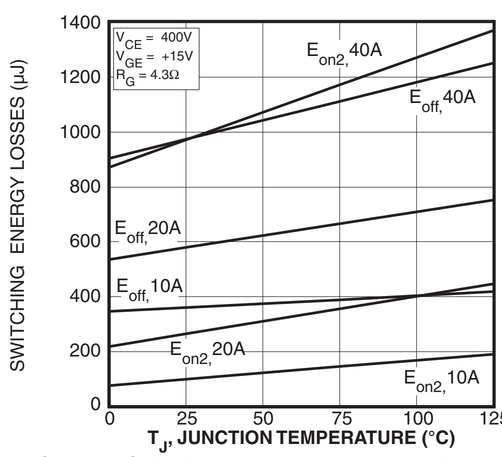


FIGURE 16, Switching Energy Losses vs Junction Temperature

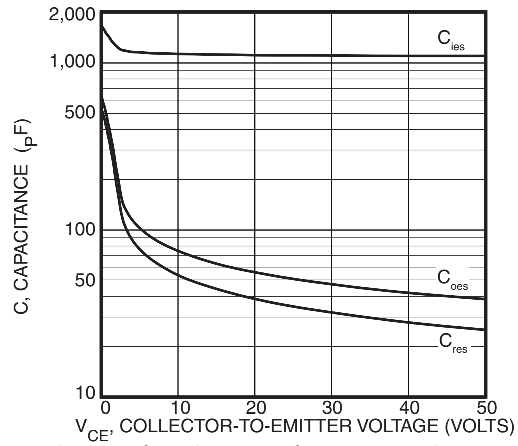


Figure 17, Capacitance vs Collector-To-Emitter Voltage

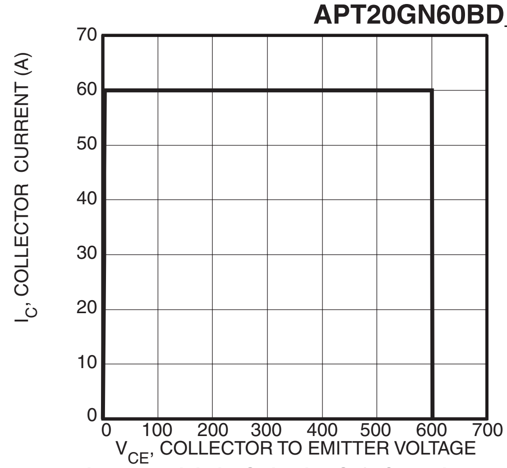


Figure 18,Minimim Switching Safe Operating Area

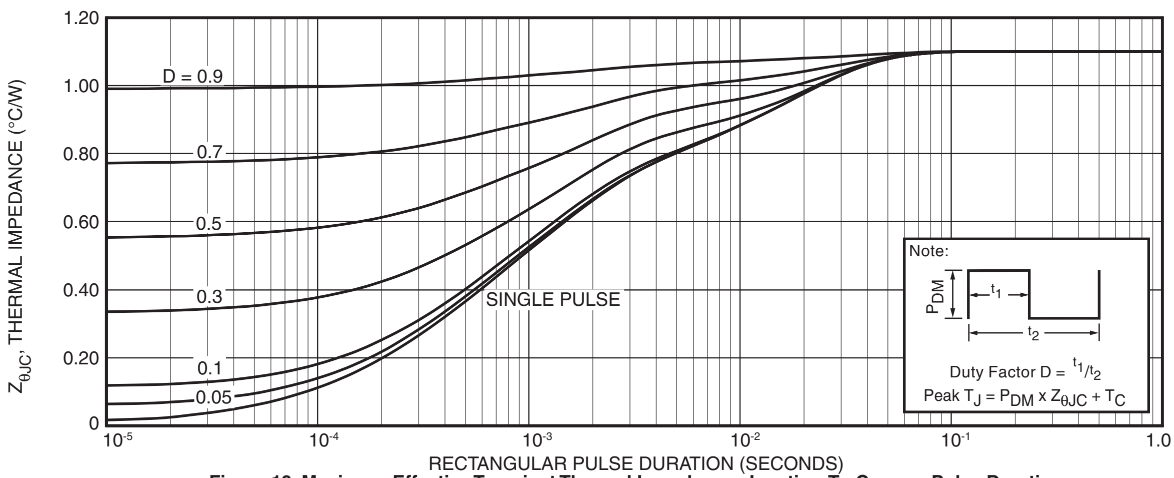
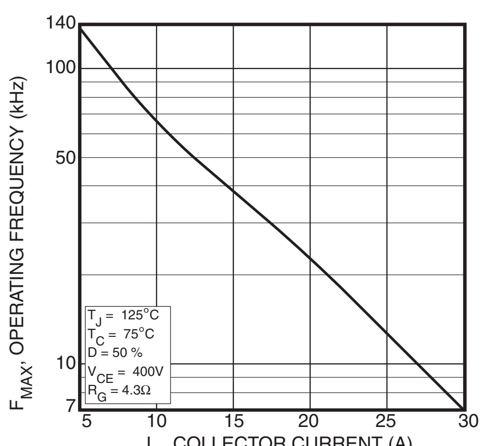


Figure 19, Maximum Effective Transient Thermal Impedance, Junction-To-Case vs Pulse Duration



$$F_{max} = \min(f_{max}, f_{max2})$$

$$f_{max1} = \frac{0.05}{t_{d(on)} + t_r + t_{d(off)} + t_f}$$

$$f_{max2} = \frac{P_{diss} - P_{cond}}{E_{on2} + E_{off}}$$

$$P_{diss} = \frac{T_J - T_C}{R_{\theta JC}}$$

Figure 20, Operating Frequency vs Collector Current

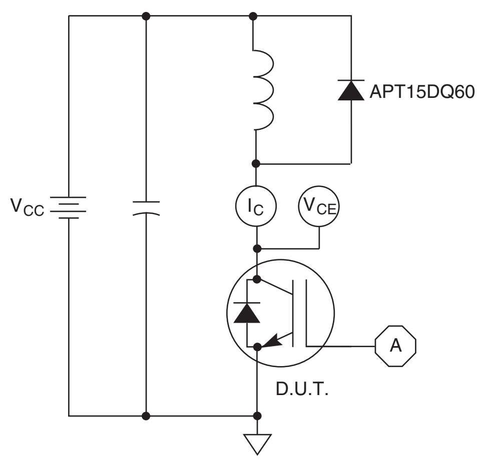


Figure 21, Inductive Switching Test Circuit

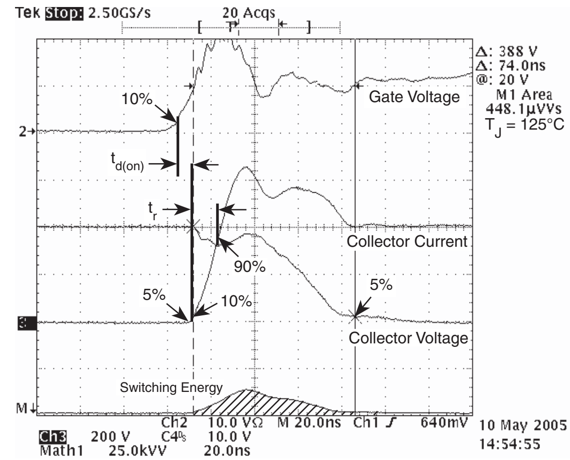


Figure 22, Turn-on Switching Waveforms and Definitions

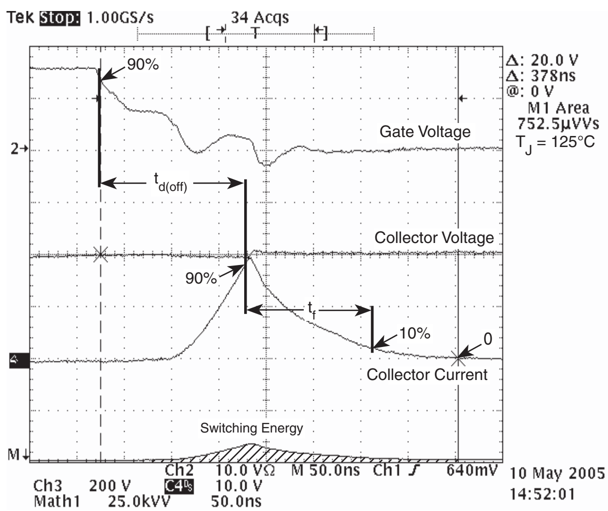


Figure 23, Turn-off Switching Waveforms and Definitions

ULTRAFAST SOFT RECOVERY ANTI-PARALLEL DIODE

MAXIMUM RATINGS

All Ratings: T_C = 25°C unless otherwise specified.

Symbol	Characteristic / Test Conditions	APT20GN60BD_SDQ1(G)	UNIT
$I_{F(AV)}$	Maximum Average Forward Current (T_C = 129°C, Duty Cycle = 0.5)	15	Amps
$I_{F(RMS)}$	RMS Forward Current (Square wave, 50% duty)	30	
I_{FSM}	Non-Repetitive Forward Surge Current (T_J = 45°C, 8.3ms)	110	

STATIC ELECTRICAL CHARACTERISTICS

Symbol	Characteristic / Test Conditions		MIN	TYP	MAX	UNIT
V_F	Forward Voltage	I_F = 20A		2.18		Volts
		I_F = 40A		2.76		
		I_F = 20A, T_J = 125°C		1.75		

DYNAMIC CHARACTERISTICS

Symbol	Characteristic	Test Conditions	MIN	TYP	MAX	UNIT
t_{rr}	Reverse Recovery Time	I_F = 1A, di_F/dt = -100A/µs, V_R = 30V, T_J = 25°C	-	15		ns
t_{rr}	Reverse Recovery Time	I_F = 15A, di_F/dt = -200A/µs V_R = 400V, T_C = 25°C	-	19		
Q_{rr}	Reverse Recovery Charge		-	21		nC
I_{RRM}	Maximum Reverse Recovery Current		-	2	-	Amps
t_{rr}	Reverse Recovery Time	I_F = 15A, di_F/dt = -200A/µs V_R = 400V, T_C = 125°C	-	105		ns
Q_{rr}	Reverse Recovery Charge		-	250		nC
I_{RRM}	Maximum Reverse Recovery Current		-	5	-	Amps
t_{rr}	Reverse Recovery Time	I_F = 15A, di_F/dt = -1000A/µs V_R = 400V, T_C = 125°C	-	55		ns
Q_{rr}	Reverse Recovery Charge		-	420		nC
I_{RRM}	Maximum Reverse Recovery Current		-	15		Amps

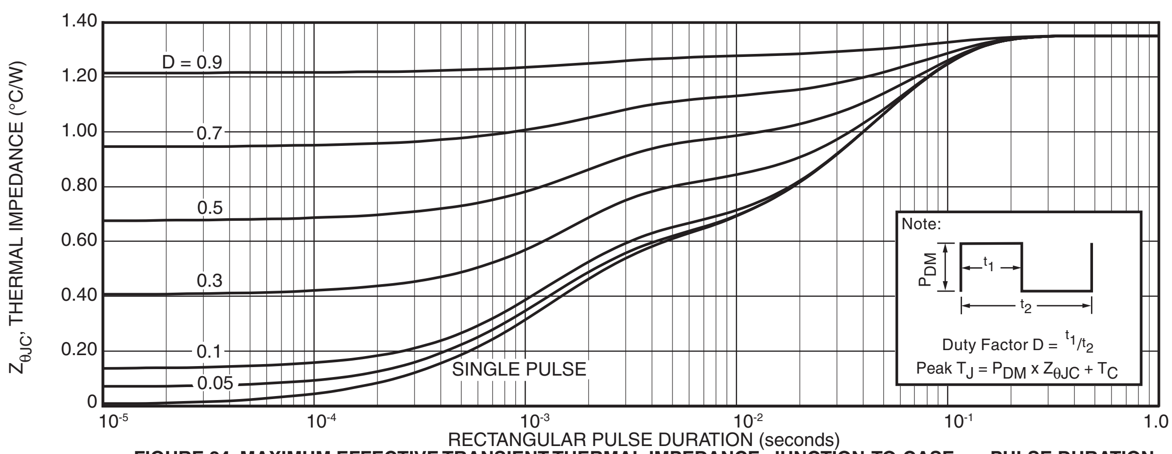


FIGURE 24. MAXIMUM EFFECTIVE TRANSIENT THERMAL IMPEDANCE, JUNCTION-TO-CASE vs. PULSE DURATION

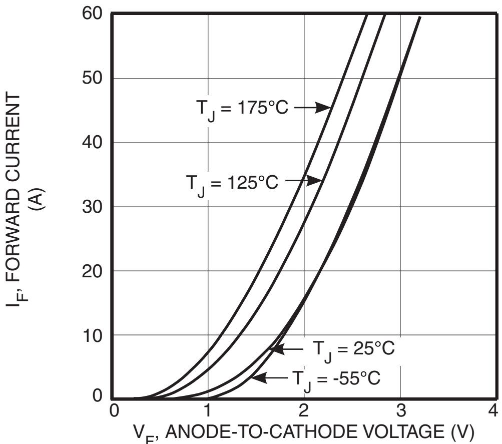


Figure 25. Forward Current vs. Forward Voltage

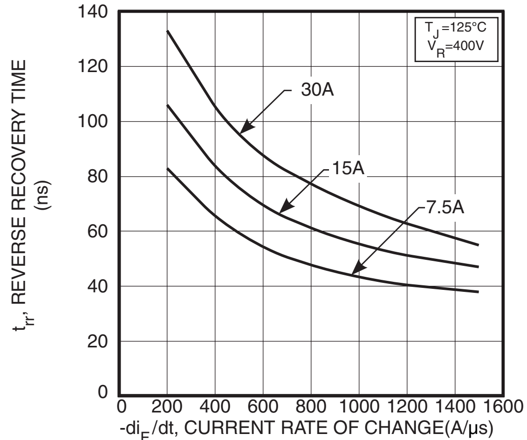


Figure 26. Reverse Recovery Time vs. Current Rate of Change

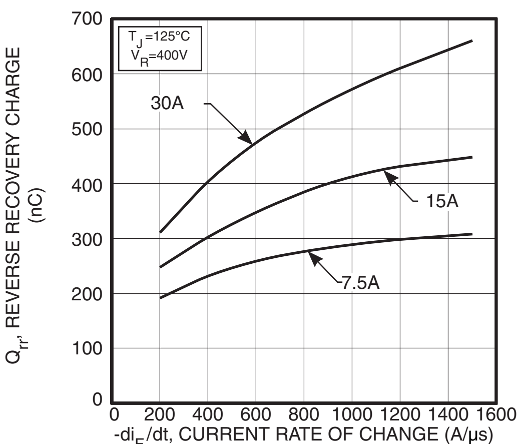


Figure 27. Reverse Recovery Charge vs. Current Rate of Change

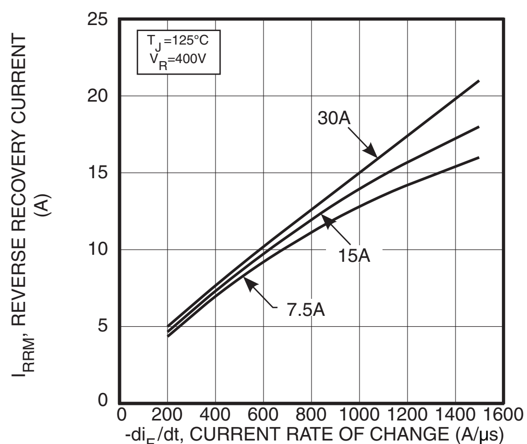


Figure 28. Reverse Recovery Current vs. Current Rate of Change

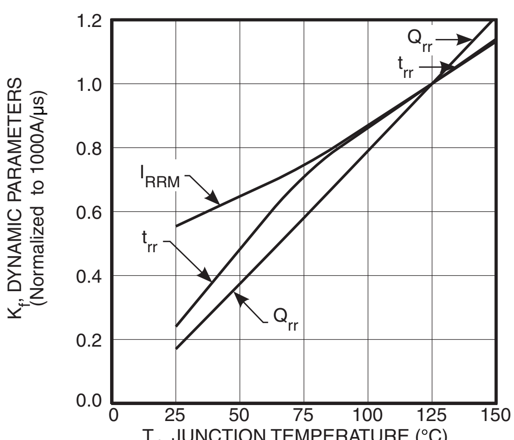


Figure 29. Dynamic Parameters vs. Junction Temperature

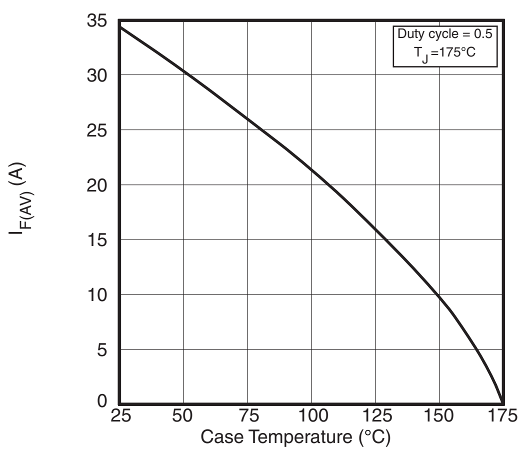


Figure 30. Maximum Average Forward Current vs. CaseTemperature

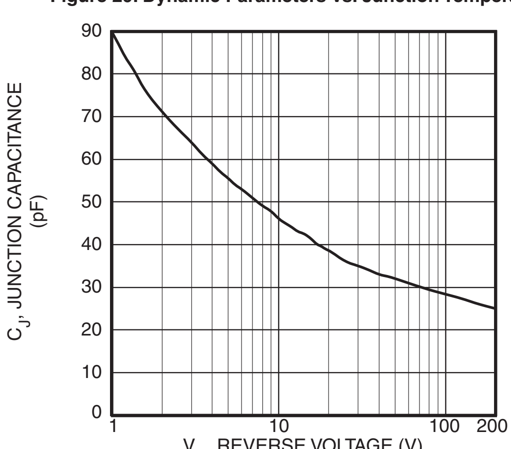


Figure 31. Junction Capacitance vs. Reverse Voltage

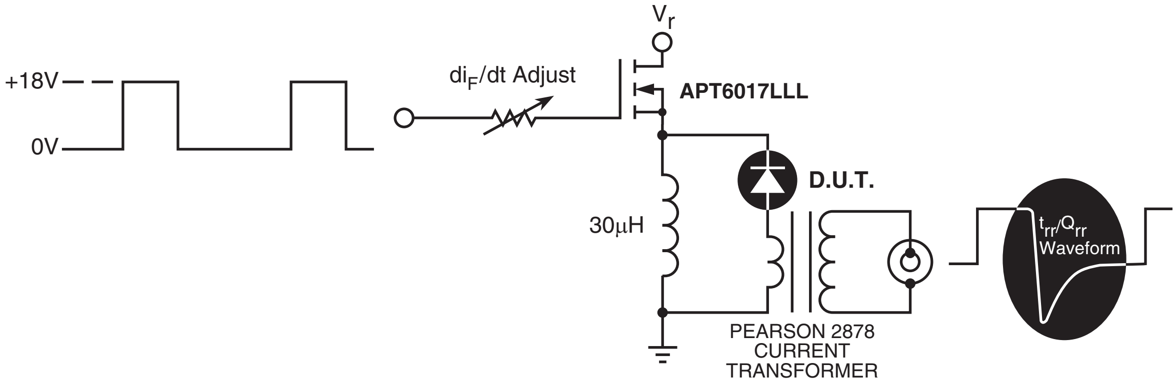


Figure 32. Diode Test Circuit

1. I_F - Forward Conduction Current
2. di_F/dt - Rate of Diode Current Change Through Zero Crossing.
3. I_{RRM} - Maximum Reverse Recovery Current.
4. t_{rr} - Reverse Recovery Time, measured from zero crossing where diode current goes from positive to negative, to the point at which the straight line through I_{RRM} and $0.25 \bullet I_{RRM}$ passes through zero.
5. Q_{rr} - Area Under the Curve Defined by I_{RRM} and t_{rr}.

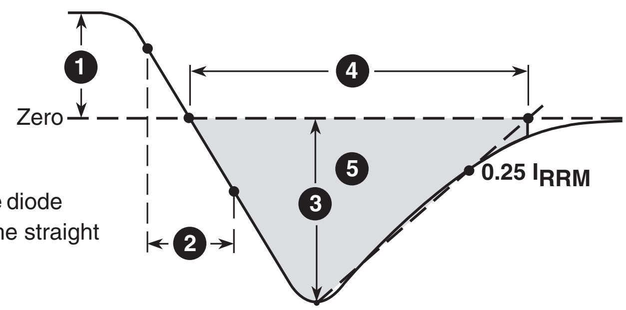
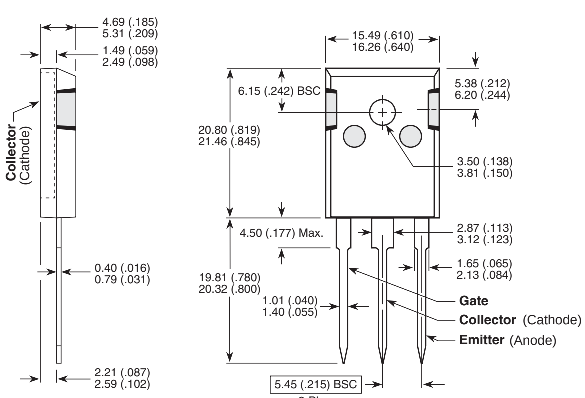


Figure 33, Diode Reverse Recovery Waveform and Definitions

TO-247 Package Outline

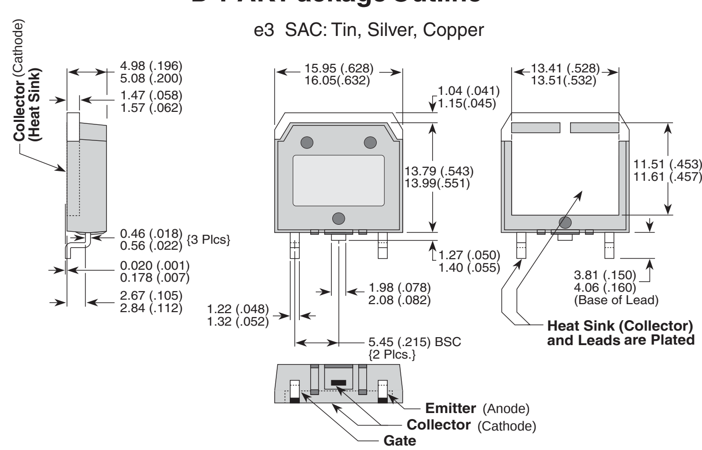
e1 SAC: Tin, Silver, Copper



Dimensions in Millimeters and (Inches)

D³PAK Package Outline

e3 SAC: Tin, Silver, Copper



Dimensions in Millimeters (Inches)

Данный компонент на территории Российской Федерации

Вы можете приобрести в компании MosChip.

Для оперативного оформления запроса Вам необходимо перейти по данной ссылке:

http://moschip.ru/get-element

Вы можете разместить у нас заказ для любого Вашего проекта, будь то серийное производство или разработка единичного прибора.

В нашем ассортименте представлены ведущие мировые производители активных и пассивных электронных компонентов.

Нашей специализацией является поставка электронной компонентной базы двойного назначения, продукции таких производителей как XILINX, Intel (ex.ALTERA), Vicor, Microchip, Texas Instruments, Analog Devices, Mini-Circuits, Amphenol, Glenair.

Сотрудничество с глобальными дистрибьюторами электронных компонентов, предоставляет возможность заказывать и получать с международных складов практически любой перечень компонентов в оптимальные для Вас сроки.

На всех этапах разработки и производства наши партнеры могут получить квалифицированную поддержку опытных инженеров.

Система менеджмента качества компании отвечает требованиям в соответствии с ГОСТ Р ИСО 9001, ГОСТ РВ 0015-002 и ЭС РД 009

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